

## ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

### Title of Invention

METHOD OF FORMING A LOW VOLTAGE GATE OXIDE  
LAYER AND TUNNEL OXIDE LAYER IN AN EEPROM CELL

Application Number : 10/717149  
Confirmation Number: 6780  
First Named Applicant: Alan Renninger  
Attorney Docket Number: ATM-262  
Art Unit: 2818  
Examiner:  
Search string: ( 5882993 or 5254489 ).pn



Certification: This Information Disclosure Statement was submitted under the following conditions, which satisfies the requirement under 37 CFR 1.97(e). The filer certified:

That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

### US Patent Documents

**Note: Applicant is not required to submit a paper copy of cited US Patent Documents**

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	5882993	1999-03-16	Gardner et al.	A1	438	591
	2	5254489	1993-10-19	Nakata	A1	437	40

### Signature

Examiner Name	Date